

# Materials and device for blue-green LED's and LD's

T. Yao

DEPARTMENT OF ELECTRICAL ENGINEERING, HIROSHIMA UNIVERSITY,  
HIGASHI-HIROSHIMA 732, JAPAN

Advance in materials science allows us to fabricate pn junctions of III-V compounds and GaN which have been considered to be difficult for last decades. As a consequence of such advances, blue-green LD's and bright GaN pure-blue LD's have been successfully fabricated. In this talk, i will address both materials and device aspects of wide-band-gap semiconductors.